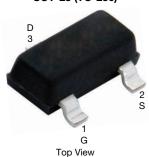


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Vishay Siliconix

Automotive P-Channel 60 V (D-S) 175 °C MOSFET

SOT-23 (TO-236)



Marking code: 9NYXX

PRODUCT SUMMARY					
V _{DS} (V)	-60				
$R_{DS(on)}$ max. (Ω) at V_{GS} = -10 V	0.335				
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5 \text{ V}$	0.500				
I _D (A)	-1.7				
Configuration	Single				

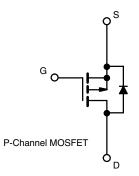
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	SQ2309CES (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unlesparameter		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	-60		
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current	T _C = 25 °C		-1.7		
	T _C = 125 °C	I _D	-1		
Continuous source current (diode conduct	I _S	-2.6	А		
Pulsed drain current ^a		I _{DM}	-6.8		
Single pulse avalanche current	. 0.4	I _{AS}	-6.8		
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	2.3	mJ	
Martin and Alexander	T _C = 25 °C	Б	2	w	
Maximum power dissipation	T _C = 125 °C	P _D	0.6	VV	
Operating junction and storage temperatu	T _J , T _{stq}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount b	R_{thJA}	166	°C/W
Junction-to-foot (drain)		R_{thJF}	73	C/ VV

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V, I}_{D} = -250 \mu\text{A}$		-60	-	-	V
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} =$	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		-2.0	-2.5	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -60 V	-	-	-1	μΑ
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -60 V, T _J = 125 °C	=	-	-50	
		V _{GS} = 0 V	V _{DS} = -60 V, T _J = 175 °C	-	-	-150	
On-state drain current a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 \text{ V}$	-5	-	-	Α
		V _{GS} = -10 V	I _D = -1.25 A	-	0.268	0.370	
Drain actives on state registance 3	Б	V _{GS} = -10 V	I _D = -1.25 A, T _J = 125 °C	-	-	0.567	Ω
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = -10 V	I _D = -1.25 A, T _J = 175 °C	-	-	0.704	
		V _{GS} = -4.5 V	I _D = -1 A	-	0.354	0.500	
Forward transconductance b	9 _{fs}	V_{DS}	= -5 V, I _D = -1 A	-	1.8	-	S
Dynamic ^b							
Input capacitance	C _{iss}			-	211	265	pF
Output capacitance	Coss	$V_{GS} = 0 V$	$V_{DS} = -25 \text{ V, f} = 1 \text{ MHz}$	-	30	40	
Reverse transfer capacitance	C _{rss}			-	21	30	
Total gate charge ^c	Qg			-	5.5	8.5	nC
Gate-source charge ^c	Q _{gs}	$V_{GS} = -10 \text{ V}$	$V_{DS} = -30 \text{ V}, I_{D} = -1 \text{ A}$	-	0.8	-	
Gate-drain charge ^c	Q_{gd}			-	1.3	-	
Gate resistance	R_g		f = 1 MHz		5.40	14.80	Ω
Turn-on delay time ^c	t _{d(on)}	$V_{DD} = -30 \text{ V}, R_L = 30 \Omega$ $I_D \cong -3 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		-	5	8	
Rise time ^c	t _r			-	9	14	ns
Turn-off delay time ^c	t _{d(off)}			-	12	18	
Fall time ^c	t _f			1	9	14	
Source-Drain Diode Ratings and Charac	teristics b						
Pulsed current ^a	I _{SM}			-	-	-6.8	Α
Forward voltage	V _{SD}	I _F = -1.5 A, V _{GS} = 0 V		-	-0.85	-1.2	V
Body diode reverse recovery time	t _{rr}	I _F = -1.2 A, di/dt = 100 A/μs		-	23	46	ns
Body diode reverse recovery charge	Qrr			-	24	48	nC
Reverse recovery fall time	ta			-	20	-	
Reverse recovery rise time	t _b			-	3	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			-	-3.1	-	Α

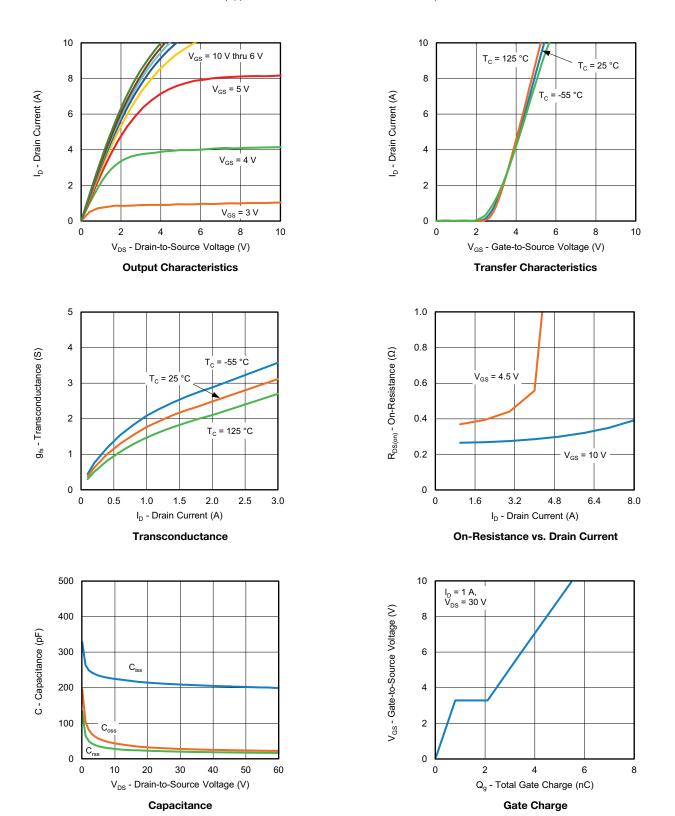
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

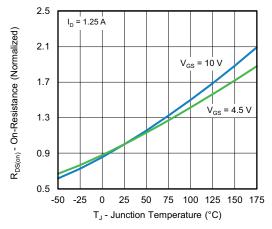


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

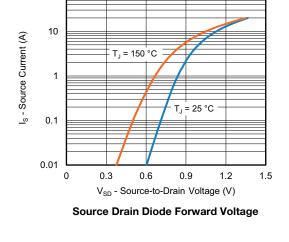




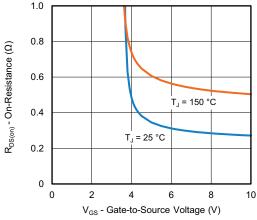
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



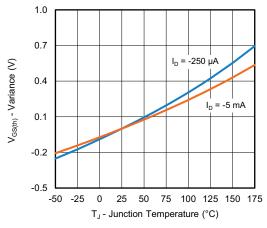
On-Resistance vs. Junction Temperature



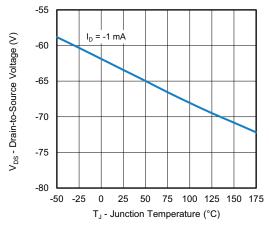
100



On-Resistance vs. Gate-to-Source Voltage



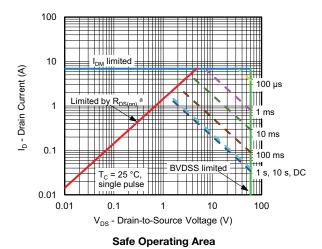
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

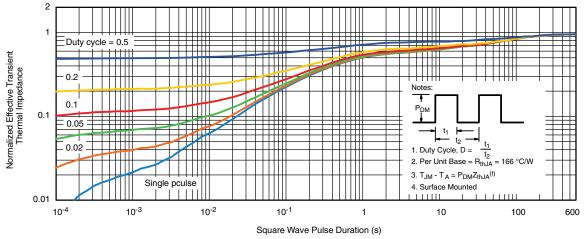


THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Note

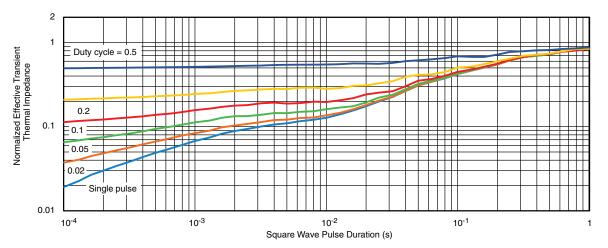
a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Notes

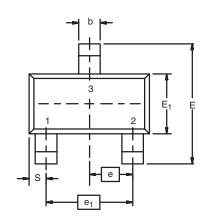
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

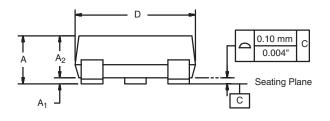
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62211.

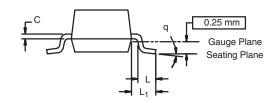


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SOT-23 (TO-236): 3-LEAD







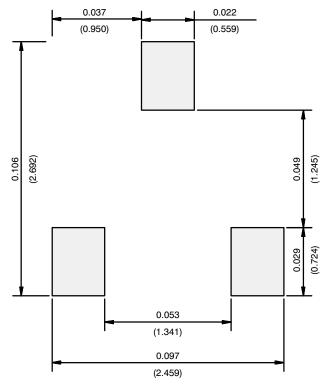
Dim	MILLIN	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.074	8 Ref	
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025	i Ref	
S	0.50 Ref		0.50 Ref 0.020 Ref) Ref
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K. 09-	Jul-01				

DWG: 5479

Document Number: 71196 www.vishay.com 09-Jul-01



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE

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